

ABSTRACT OF THE DISCLOSURE

The present invention is a method for producing a single crystal by Czochralski method with pulling a seed crystal from a raw material melt, wherein when a pulling rate of pulling a single crystal is defined as V (mm/min), a temperature gradient at a solid-liquid interface is defined as G (K/mm) and a highest temperature at an interface between a crucible and a raw material melt is defined as T_{max} ($^{\circ}C$), at least, a range of a value of V/G ($mm^2/K \cdot min$) including a desired defect region and/or a desired defect-free region is determined according to the T_{max} ($^{\circ}C$), and the single crystal is pulled with controlling a value of V/G ($mm^2/K \cdot min$) within the determined range. There can be provided a method for producing a single crystal in which when a single crystal is pulled with controlling a value of V/G , a value of V/G including a desired defect region and/or a desired defect-free region can be determined more precisely and a single crystal with desired quality can be more surely pulled.